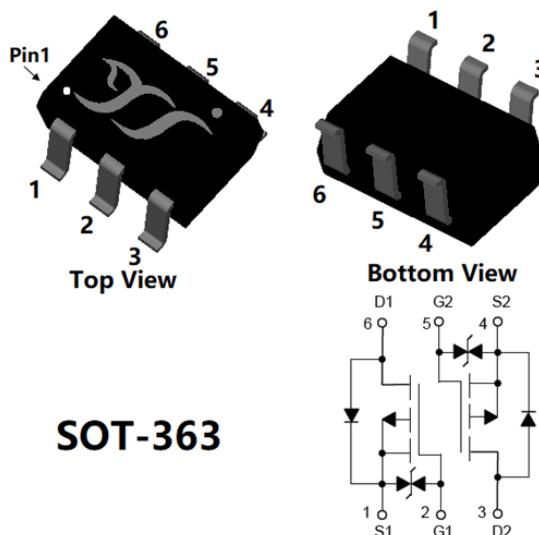


## P-Channel and P-Channel Complementary MOSFET



### Product Summary

- $V_{DS}$  -60V
- $I_D$  -0.32A
- $R_{DS(on)}$  (at  $V_{GS}=-10V$ )  $<3\Omega$
- $R_{DS(on)}$  (at  $V_{GS}=-4.5V$ )  $<3.5\Omega$
- Gate-Source ESD Rating Up to 2KV (HBM)

### General Description

- P-Channel Switch with Low  $R_{DS(on)}$
- Epoxy Meets UL 94 V-0 Flammability Rating
- Moisture Sensitivity Level 1
- Halogen Free

### Applications

- Power management
- Portable equipment

#### ■ Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		$V_{DS}$	-60	V
Gate-source Voltage		$V_{GS}$	$\pm 20$	V
Drain Current	$T_A=25^\circ C$	$I_D$	-0.32	A
	$T_A=100^\circ C$		-0.2	
Pulsed Drain Current <sup>A</sup>		$I_{DM}$	-1.2	A
Total Power Dissipation <sup>B</sup>	$T_A=25^\circ C$	$P_D$	0.41	W
	$T_A=100^\circ C$		0.16	
Junction and Storage Temperature Range		$T_J, T_{STG}$	-55~+150	°C

#### ■ Thermal resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient <sup>C</sup>	Steady-State	$R_{\theta JA}$	250	300	°C/W

#### ■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
BSS84KDWJ	F2	84K	3000	30000	120000	7" reel



# BSS84KDwj

## ■ Electrical Characteristics ( $T_J=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Static Parameter</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-60	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-60V, V_{GS}=0V$	-	-	-1	$\mu A$
		$V_{DS}=-60V, V_{GS}=0V, T_J=150^\circ C$	-	-	-100	
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 10$	$\mu A$
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1	-1.5	-2	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-0.32A$	-	2.2	3	$\Omega$
		$V_{GS}=-4.5V, I_D=-0.2A$	-	2.5	3.5	
Diode Forward Voltage	$V_{SD}$	$I_S=-0.32A, V_{GS}=0V$	-	-0.9	-1.3	V
Gate resistance	$R_G$	f=1MHz, Open drain	-	700	-	$\Omega$
Maximum Body-Diode Continuous Current	$I_S$		-	-	-0.32	A
<b>Dynamic Parameters</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=-30V, V_{GS}=0V, f=1MHz$	-	35	-	$pF$
Output Capacitance	$C_{oss}$		-	6	-	
Reverse Transfer Capacitance	$C_{rss}$		-	3	-	
<b>Switching Parameters</b>						
Total Gate Charge	$Q_g$	$V_{GS}=-10V, V_{DS}=-30V, I_D=-1A$	-	1.7	-	$nC$
Gate-Source Charge	$Q_{gs}$		-	0.6	-	
Gate-Drain Charge	$Q_{gd}$		-	0.2	-	
Reverse Recovery Charge	$Q_{rr}$	$I_F=-1A, di/dt=100A/us$	-	10	-	$nC$
Reverse Recovery Time	$t_{rr}$		-	18	-	ns
Turn-on Delay Time	$t_{D(on)}$	$V_{GS}=-10V, V_{DD}=-30V, I_D=-1A, R_{GEN}=2.3\Omega$	-	6	-	ns
Turn-on Rise Time	$t_r$		-	21	-	
Turn-off Delay Time	$t_{D(off)}$		-	31	-	
Turn-off fall Time	$t_f$		-	32	-	

A. Repetitive rating; pulse width limited by max. junction temperature.

B.  $P_d$  is based on max. junction temperature, using junction-case and junction-ambient thermal resistance.

C. The value of  $R_{GJA}$  is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in the still air environment with  $T_A=25^\circ C$ .

The maximum allowed junction temperature of  $150^\circ C$ . The value in any given application depends on the user's specific board design.

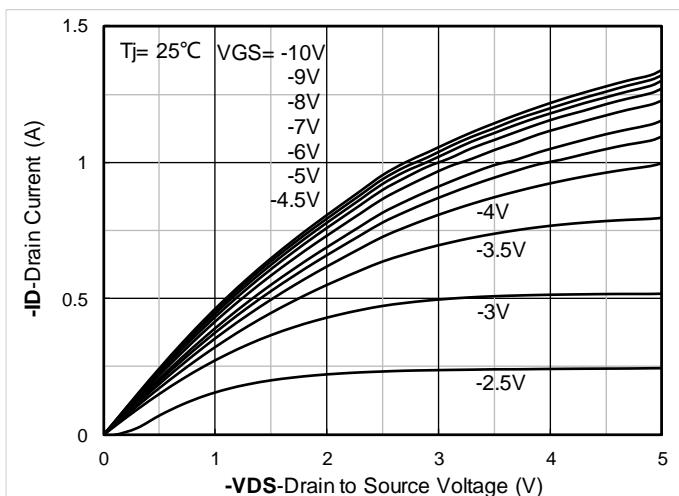
**■Typical Electrical and Thermal Characteristics Diagrams**

Figure 1. Output Characteristics

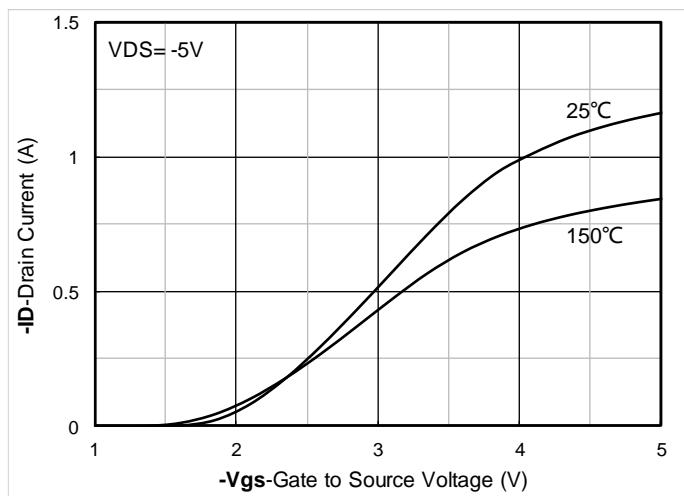


Figure 2. Transfer Characteristics

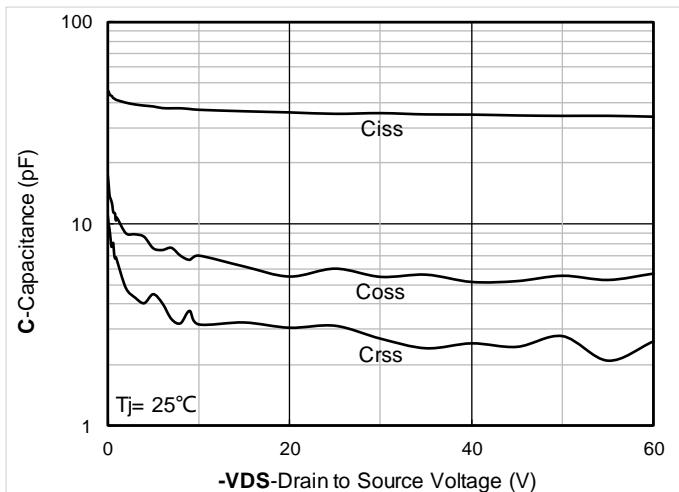


Figure 3. Capacitance Characteristics

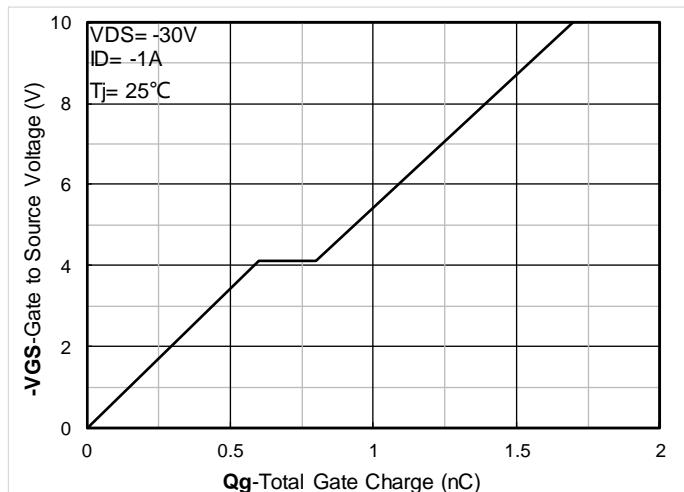


Figure 4. Gate Charge

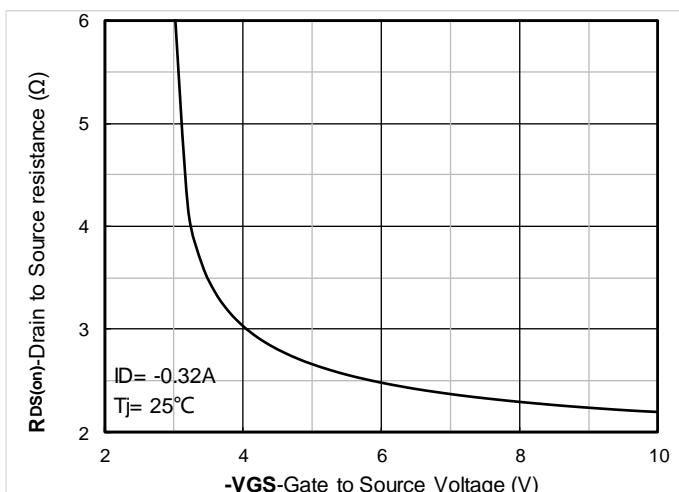


Figure 5. On-Resistance vs Gate to Source Voltage

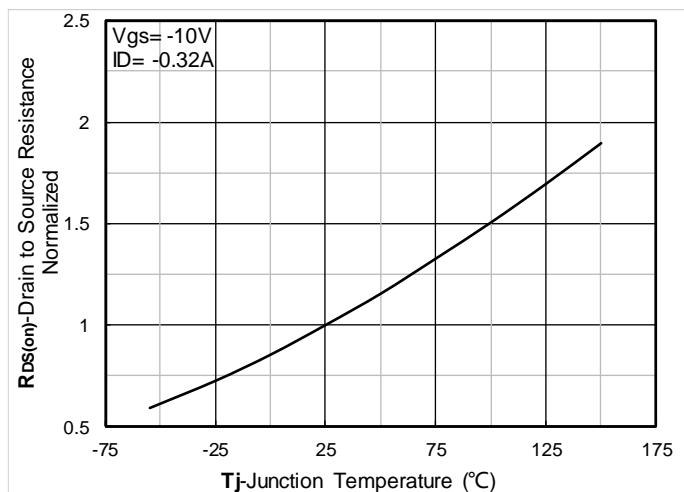


Figure 6. Normalized On-Resistance

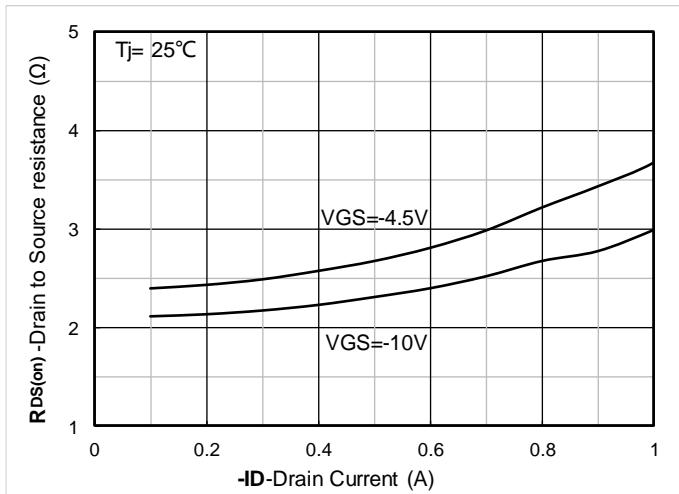


Figure 7. RDS(on) VS Drain Current

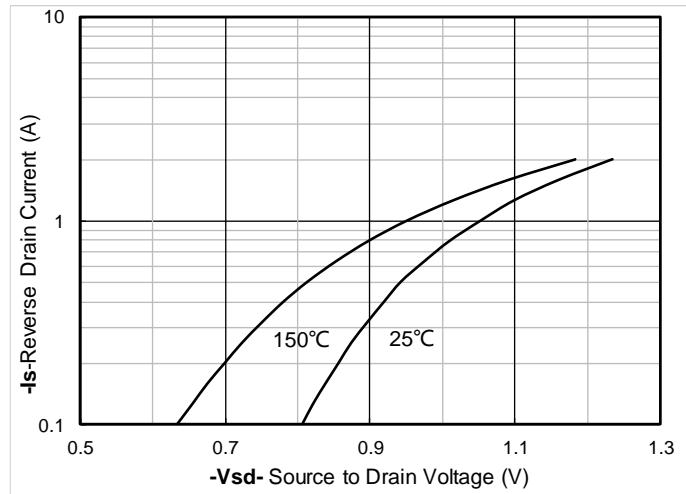


Figure 8. Forward characteristics of reverse diode

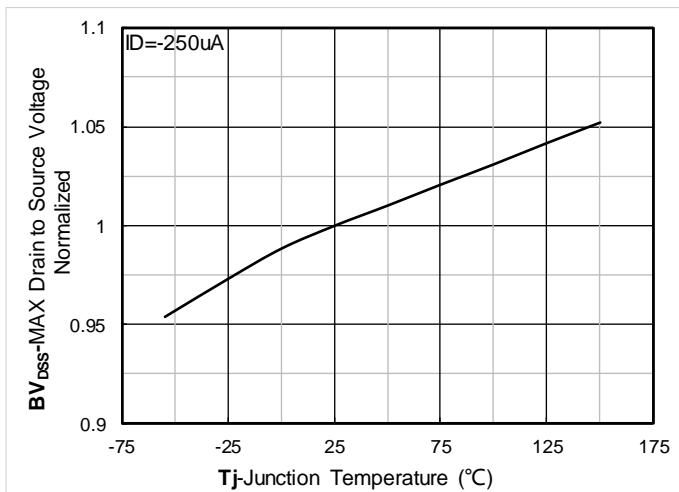


Figure 9. Normalized breakdown voltage

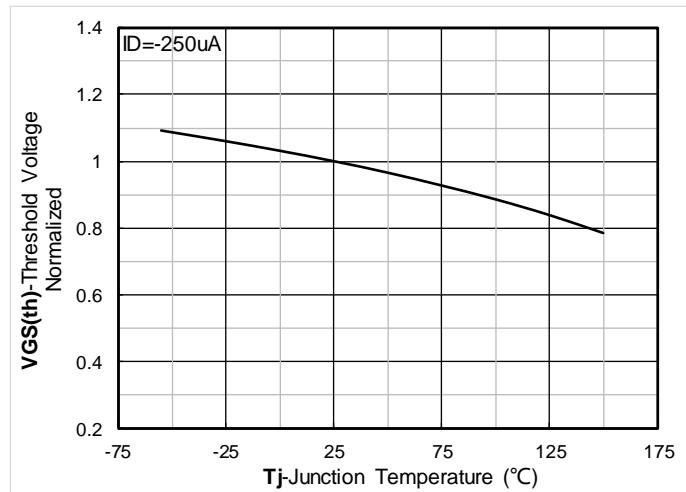


Figure 10. Normalized Threshold voltage

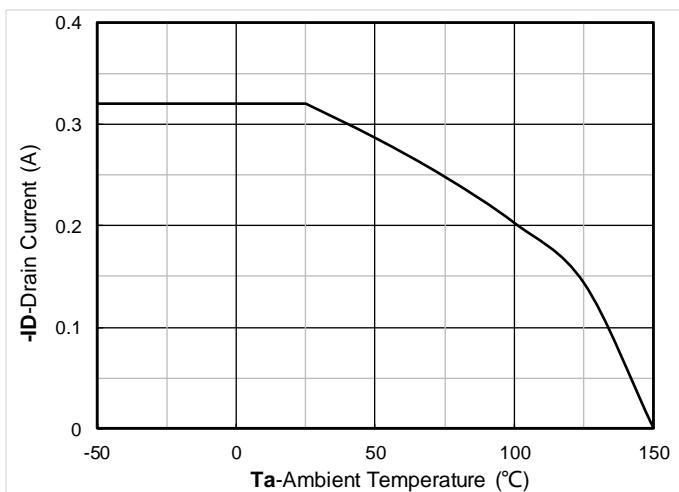


Figure 11. Current dissipation

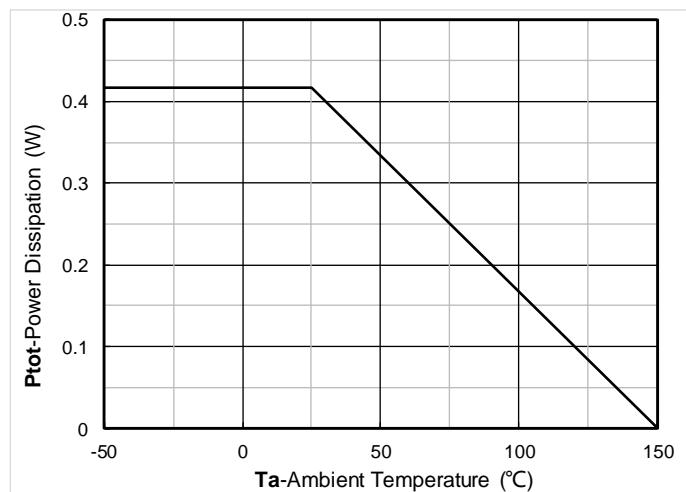


Figure 12. Power dissipation

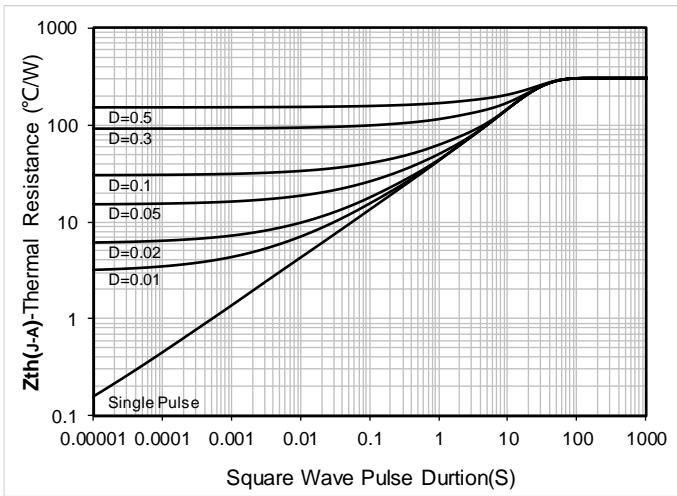


Figure 13. Maximum Transient Thermal Impedance

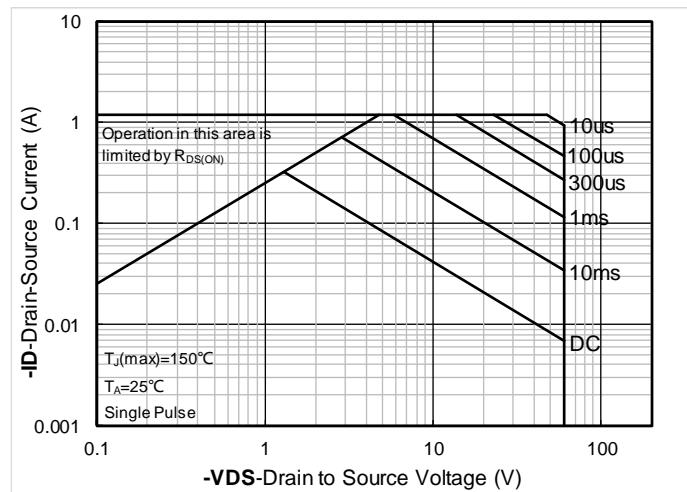
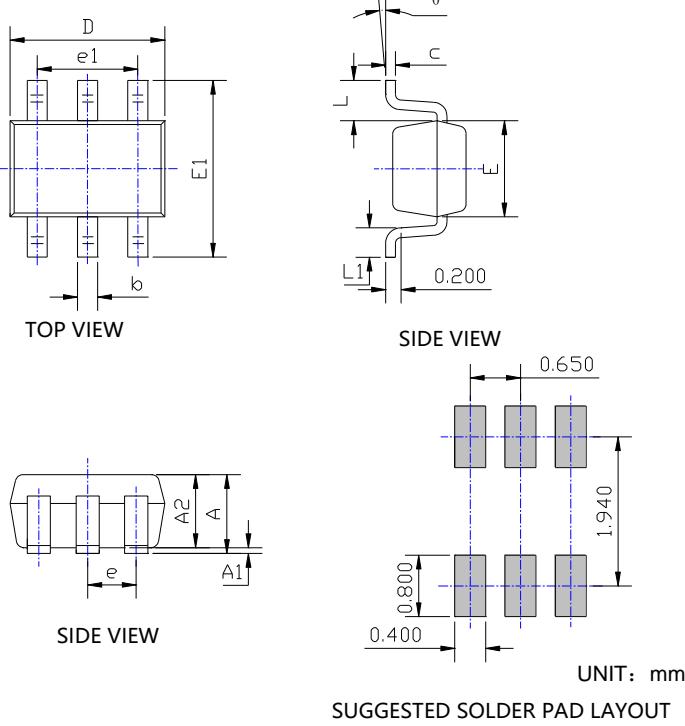


Figure 14. Safe Operation Area

**■ SOT-363 Package information**

SYMBOL	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.035	0.043	0.900	1.100
A1	0.000	0.004	0.000	0.100
A2	0.035	0.039	0.900	1.000
b	0.006	0.014	0.150	0.350
c	0.004	0.010	0.100	0.250
D	0.071	0.087	1.800	2.200
E	0.045	0.053	1.150	1.350
E1	0.085	0.096	2.150	2.450
e	0.026TYP		0.650TYP	
e1	0.047	0.055	1.200	1.400
L	0.021REF		0.525REF	
L1	0.010	0.018	0.260	0.460
θ	0°	8°	0°	8°

**NOTE:**

- 1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
- 2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
- 3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.



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